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RoHS

COMPLIANT

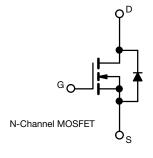
### Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.00112
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.00161
I <sub>D</sub> (A)	350
Configuration	Single
Package	PowerPAK SO-8L

#### **FEATURES**

- TrenchFET<sup>®</sup> Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATING	<b>GS</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	l)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain current	T <sub>C</sub> = 25 °C	1	350		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	261		
Continuous source current (diode conduction)		I <sub>S</sub>	324	А	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	600		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	42		
Single pulse avalanche energy		E <sub>AS</sub>	84	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	Р	500	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	166	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) <sup>c</sup>			260	U	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	68	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	0.3	0/10

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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### SQJ136ELP

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•					1
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.2	1.7	2.2	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	= 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-source on-state resistance <sup>a</sup>		$V_{GS} = 10 V$	I <sub>D</sub> = 15 A	-	0.0009	0.00112	
	Б	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.00200	Ω
	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.00244	52
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 15 A - 0.00124 0.00161				
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	30	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	5725	8015	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	1790	2505	
Reverse transfer capacitance	C <sub>rss</sub>	-	F		183	256	1
Total gate charge <sup>c</sup>	Qg			-	107	150	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 40 \text{ A}$	-	17.5	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	19	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz	0.67	1.48	2.40	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_{\text{L}} = 0.5 \ \Omega$ $\text{I}_{\text{D}} \cong 40 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \ \Omega$		-	13	19	- ns
Rise time <sup>c</sup>	tr			-	16	23	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	50	71	
Fall time <sup>c</sup>	t <sub>f</sub>			-	14	20	
Source-Drain Diode Ratings and Cha	aracteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	600	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 40 A, di/dt = 100 A/μs		-	57	80	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	62	86	nC
Reverse recovery fall time	t <sub>a</sub>			-	26	37	
Reverse recovery rise time	t <sub>b</sub>	1		-	31	42	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	1.8	2.6	А

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

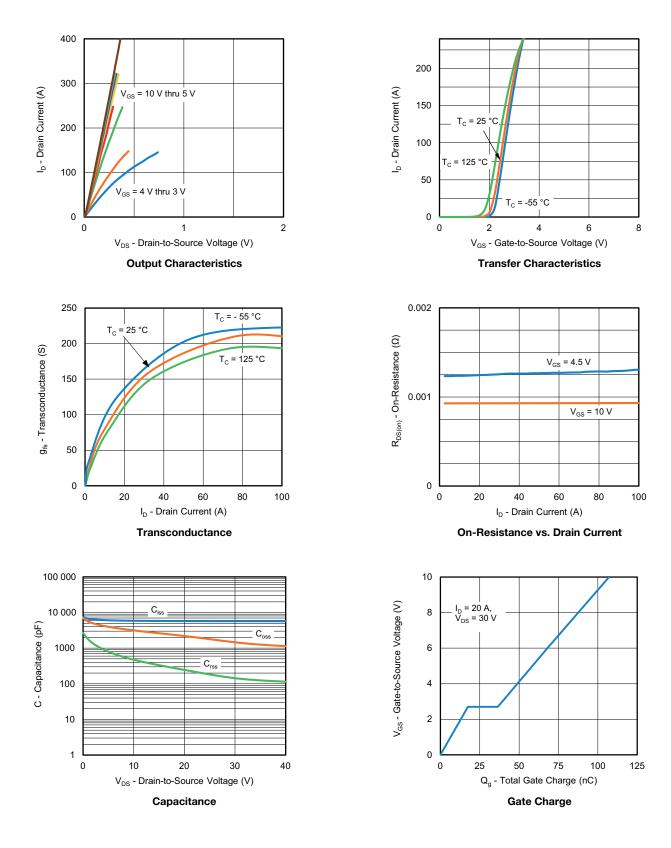
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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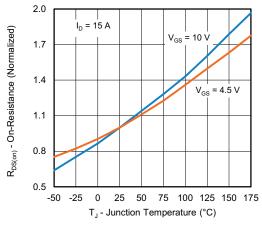
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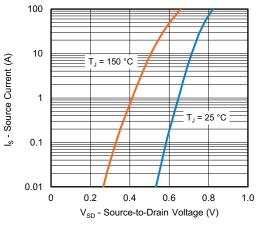


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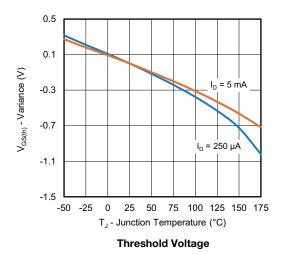
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



**On-Resistance vs. Junction Temperature** 



Source Drain Diode Forward Voltage



Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

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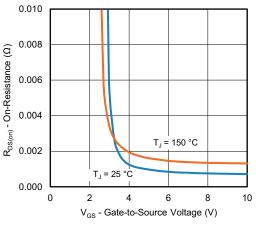
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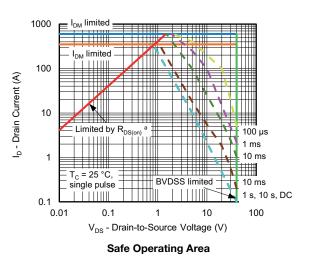
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T<sub>J</sub> - Junction Temperature (°C)

Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to Source Voltage

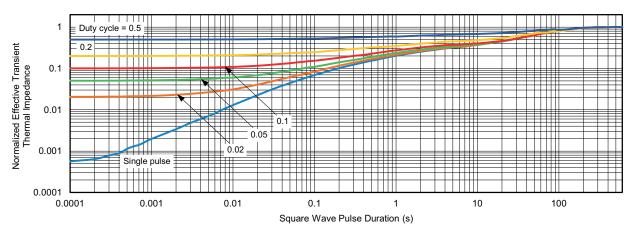


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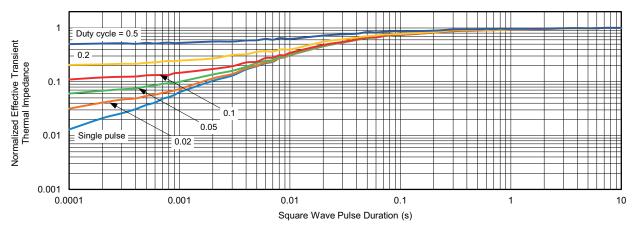


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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

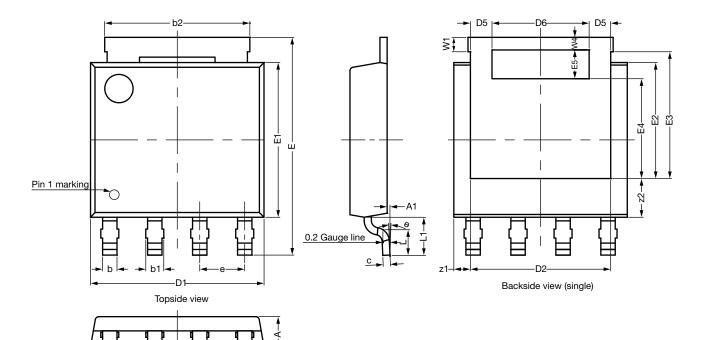
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# PowerPAK<sup>®</sup> SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
А	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

Note

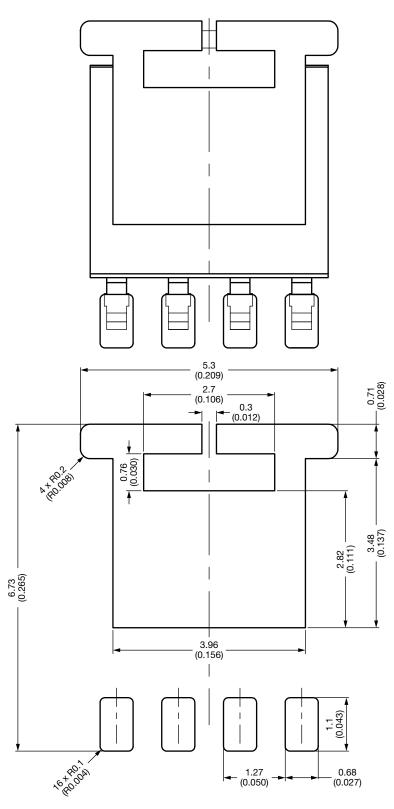
• Millimeter will govern

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## **Recommended Land Pattern PowerPAK® SO-8L Single Short Ear**



Dimensions in Millimeters (Inches)

Revision: 24-Aug-2021

Document Number: 78020



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